2048-BIT BIPOLAR RAM (256×8) 8X350 (T.S.)

DESCRIPTION

The 8X350 bipolar RAM is designed principally as a working storage element in an 8X300 based system. Internal circuitry is provided for direct use in 8X300 applications. When used with the 8X300, the RAM address and data buses are tied together and connected to the IV bus of the system.

The data inputs and outputs share a common I/O bus with 3-state outputs.

The 8X350 is available in commercial and military temperature ranges. For the commercial temperature range (0°C to +75°C) specify N8X350-F, and for the military temperature range (−55°C to +125°C) specify S8X350-F.

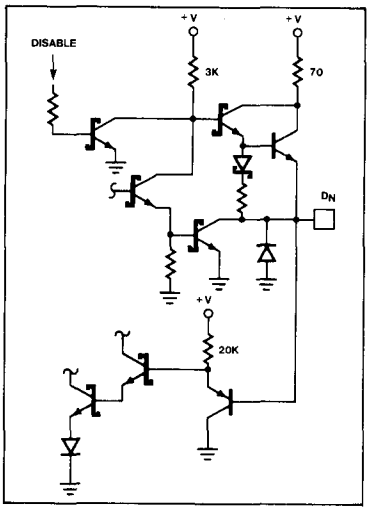
FEATURES

- **On-chip address latches**
- **3-state outputs**
- **Schottky clamped TTL**
- **Internal control logic for 8X300 system**
- **Directly interfaces with the 8X300 bipolar microprocessor with no external logic**
- **May be used on left or right bank**

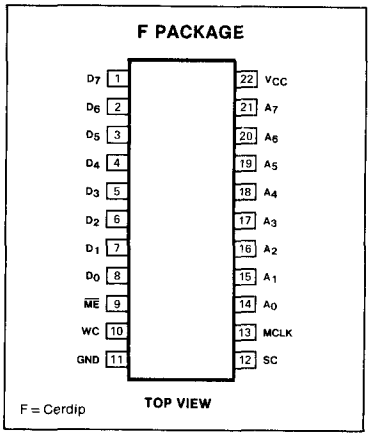
APPLICATIONS

- **8X300 or 8X305 working storage**

TYPICAL I/O STRUCTURE



PIN CONFIGURATION



ABSOLUTE MAXIMUM RATINGS

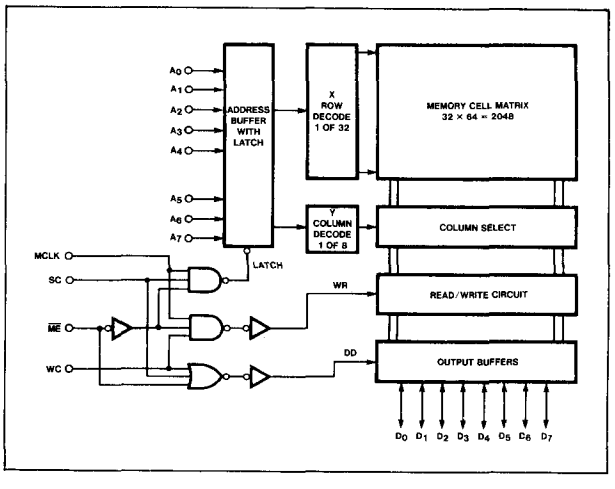
PARAMETER		RATING	UNIT
V_{CC}	Supply voltage	+7	Vdc
V_{IN}	Input voltage	+5.5	Vdc
	Output voltage		Vdc
V_{OH}	High	+5.5	
V_O	Off-state	+5.5	
	Temperature range		°C
T_A	Operating		
	Commercial	0 to +75	
	Military	−55 to +125	
T_{STG}	Storage	−65 to +150	

TRUTH TABLE

Note X = Don't care

MODE	$\overline{ME}$	SC	WC	MCLK	BUSSED DATA/ADDRESS LINES
Hold address Disable data out	1	X	X	X	High Z data out
Input new address	0	1	0	1	Address High Z
Hold address Disable data out	0	1	0	0	High Z data out
Hold address Write data	0	0	1	1	Data in
Hold address Disable data out	0	0	1	0	High Z data out
Hold address Read data	0	0	0	X	Data out
Undefined state[12]	0	1	1	1	—
Hold address[12] Disable data out	0	1	1	0	High Z data out

BLOCK DIAGRAM



DC ELECTRICAL CHARACTERISTICS[2]

N8X350: 0°C ≤ T_A ≤ +75°C, 4.75V ≤ V_{CC} ≤ 5.25V
S8X350: −55°C ≤ T_A ≤ +125°C, 4.75V ≤ V_{CC} ≤ 5.25V

PARAMETER		TEST CONDITIONS	N8X350			S8X350			UNIT
			Min	Typ	Max	Min	Typ	Max	
	Input voltage								V
V_{IL}	Low[1]	V_{CC} = Min			.85			.80	
V_{IH}	High[1]	V_{CC} = Max	2.0			2.0			
V_{IC}	Clamp[1,3]	V_{CC} = Min, I_{IN} = −12mA			−1.2			−1.2	
	Output voltage	V_{CC} = Min							V
V_{OL}	Low[1,4]	I_{OL} = 9.6mA			0.5			.5	
V_{OH}	High[1,5]	I_{OH} = −2mA	2.4			2.4			
	Input current								μA
I_{IL}	Low	V_{IN} = 0.45V			−100			−150	
I_{IH}	High	V_{IN} = 5.5V			25			50	
	Output current								μA
$I_{O(OFF)}$	High Z state	$\overline{ME}$ = High, V_{OUT} = 5.5 V			40			60	μA
		$\overline{ME}$ = High, V_{OUT} = 0.5 V			−100			−100	
I_{OS}	Short circuit[3,6]	SC = WC, $\overline{ME}$ = Low, V_{OUT} = 0V, Stored High	−20		−70	−15		−85	mA
I_{CC}	V_{CC} supply current[7]	V_{CC} = Max			185			200	mA
	Capacitance	$\overline{ME}$ = High, V_{CC} = 5.0V							pF
C_{IN}	Input	V_{IN} = 2.0V		5			5		
C_{OUT}	Output	V_{OUT} = 2.0V		8			8		

AC ELECTRICAL CHARACTERISTICS[2,9]

N8X350: 0°C ≤ T_A ≤ +75°C, 4.75V ≤ V_{CC} ≤ 5.25V R_1 = 470Ω, R_2 = 1kΩ, C_L = 30pF
S8X350: −55°C ≤ T_A ≤ +125°C, 4.75V ≤ V_{CC} ≤ 5.25V

PARAMETER		TO	FROM	N8X350			S8X350			UNIT
				Min	Typ	Max	Min	Typ	Max	
	Enable time									ns
T_{E1}	Output	Data out	SC−			35			40	
T_{E2}	Output	Data out	$\overline{ME}$−			35			40	
	Disable time									ns
T_{D1}	Output	Data out	SC+			35			40	
T_{D2}	Output	Data out	$\overline{ME}$+			35			40	
	Pulse width									ns
T_W	Master clock[8]			40			50			
	Setup and hold time									ns
T_{SA}	Setup time	MCLK−	Address	30			40			
T_{HA}	Hold time	Address	MCLK−	5			10			
T_{SD}	Setup time	MCLK−	Data in	35			45			
T_{HD}	Hold time	Data in	MCLK−	5			10			
T_{S3}	Setup time	MCLK−	$\overline{ME}$−	40			50			
T_{H3}	Hold time	$\overline{ME}$+	MCLK−	5			5			
T_{S1}	Setup time	MCLK−	$\overline{ME}$−	30			40			
T_{H2}	Hold time	$\overline{ME}$−	MCLK−	5			5			
T_{S2}	Setup time	$\overline{ME}$−	SC−,WC−	0			5			
T_{H1}	Hold time	SC−	MCLK−	5			5			
T_{H4}	Hold time	WC−	MCLK−	5			5			

Notes on following page.

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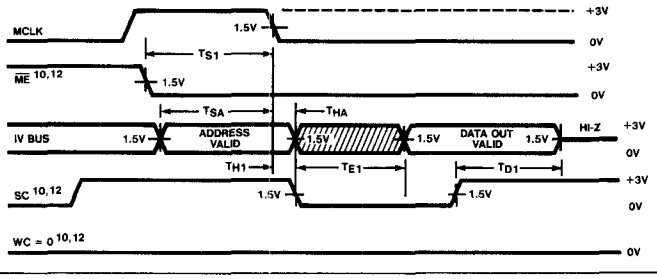
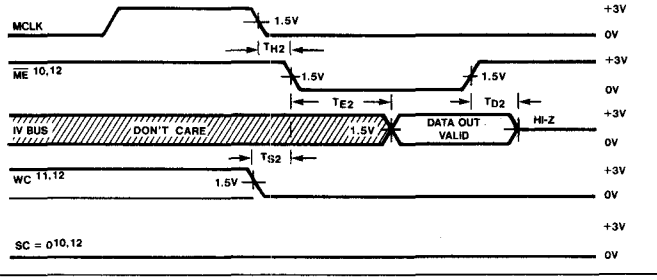
TIMING DIAGRAMS

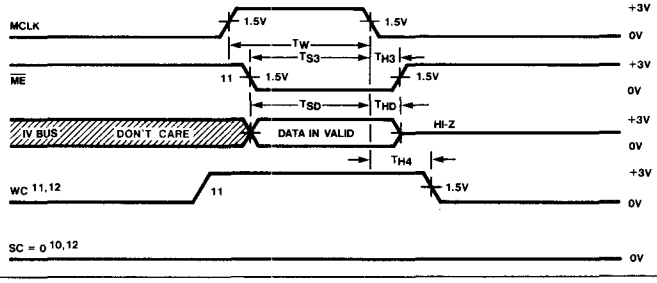
TRANSPARENT ADDRESS READ CYCLE



LATCHED ADDRESS READ CYCLE



LATCHED ADDRESS WRITE CYCLE



NOTES

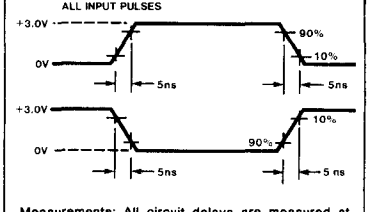
1. All voltage values are with respect to network ground terminal.
2. The operating ambient temperature ranges are guaranteed with transverse air flow exceeding 400 linear feet per minute and a 2-minute warm-up.
   Typical thermal resistance values of the package at maximum temperature are:
   Θ_{JA} junction to ambient at 400fpm air flow - 50°C/watt
   Θ_{JA} junction to ambient - still air - 90°C/watt
   Θ_{JA} junction to case - 20°C/watt
3. Test each pin one at a time.
4. Measured with a logic low stored Output sink current is supplied through a resistor to V_{CC}.
5. Measured with a logic high stored.
6. Duration of the short circuit should not exceed 1 second.
7. I_{CC} is measured with the write enable and memory enable inputs grounded, all other inputs at 4.5V and the output open.
8. Minimum required to guarantee a Write into the slowest bit.
9. Applied to the 8X300 based system with the data and address pins tied to the IV Bus.
10. SC + $\overline{ME}$ = 1 to avoid bus conflict.
11. WC + $\overline{ME}$ = 1 to avoid bus conflict.
12. The SC and WC outputs from the 8X300 are never at 1 simultaneously.

TIMING DEFINITIONS

T_{S1}	Required delay between beginning of Master Enable low and falling edge of Master Clock.
T_{SA}	Required delay between beginning of valid address and falling edge of Master Clock.
T_{HA}	Required delay between falling edge of Master Clock and end of valid Address.
T_{H1}	Required delay between falling edge of Master Clock and when Select Command becomes low.
T_{E1}	Delay between beginning of Select Command low and beginning of valid data output on the IV Bus.
T_{D1}	Delay between when select Command becomes high and end of valid data output on the IV Bus.
T_{H2}	Required delay between falling edge of Master Clock and when Master Enable becomes low.
T_{E2}	Delay between when Master Enable becomes low and beginning of valid data output on the IV Bus.
T_{D2}	Delay between when Master Enable becomes high and end of valid data output on the IV Bus.
T_{S2}	Required delay between when Select Command or Write Command becomes low and when Master Enable becomes low.
T_W	Minimum width of the Master Clock pulse.
T_{S3}	Required delay between when Master Enable becomes low and falling edge of Master Clock.
T_{H3}	Required delay between falling edge of Master Clock and when Master Enable becomes high.
T_{SD}	Required delay between beginning of valid data input on the IV Bus and falling edge of Master Clock.
T_{HD}	Required delay between falling edge of Master Clock and end of valid data input on the IV Bus.
T_{H4}	Required delay between falling edge of Master Clock and when Write Command becomes low.

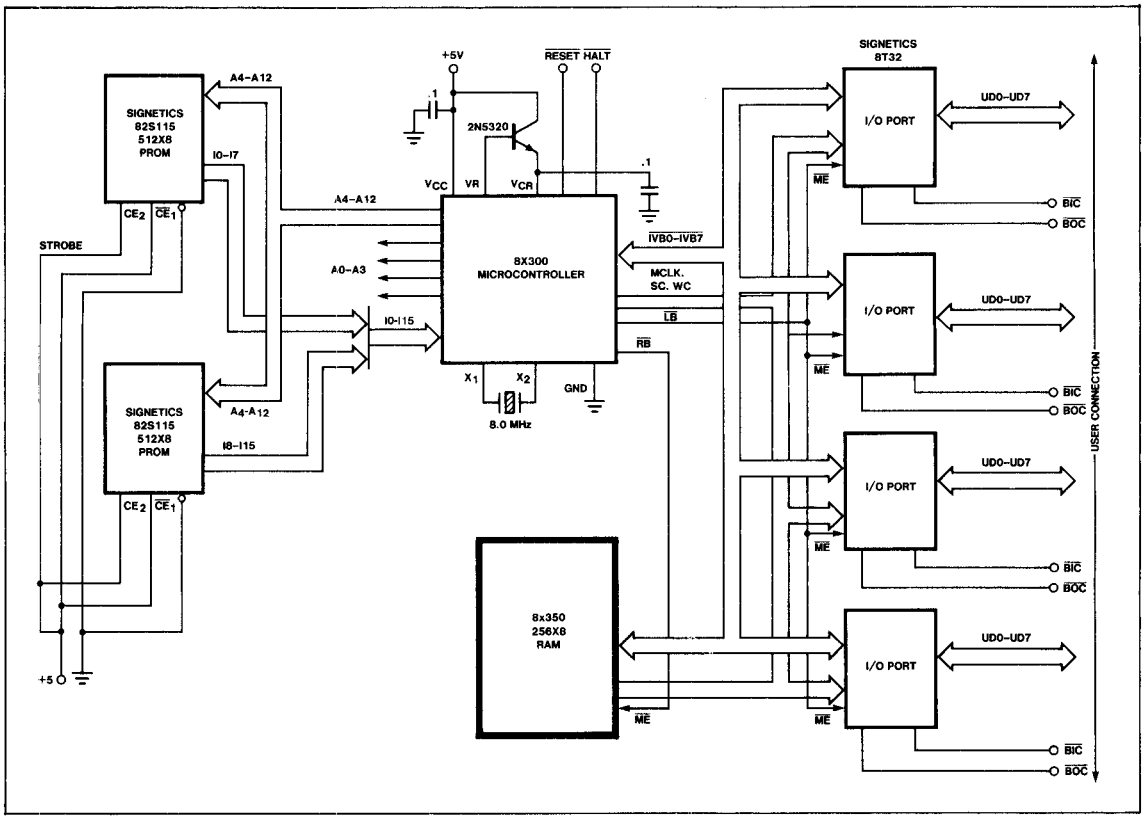
VOLTAGE WAVEFORM

INPUT PULSES



Measurements: All circuit delays are measured at the +1.5V level of inputs and output.

TYPICAL 8X350 APPLICATION



TEST LOAD CIRCUIT